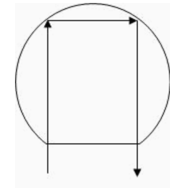
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Notch or Flat	Notch	Wafer Vendor
	3.0	Notch Direction	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	N	Wafer Vendor
	6.0	Dopant	Phosphorous	Wafer Vendor
	7.0	Resistivity	1~ 10 ohm cm	Wafer Vendor
	8.0	Overall Thickness	675.00 +/- 5.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<10.00um	Guaranteed by process
	9.1	Bow	<50.00um	ADE
	9.2	Warp	<50.00um	ADE
	10.0	Orientation	<100> +/-0.5	Wafer Vendor
	11.0	Back Surface Quality	Lapped / Etched	Wafer Vendor
	12.0	Lasermarking	Backside, Format: PPT-PNS-XXXX-XX	Guaranteed by process, see additional notes.
	13.0	Front Surface Quality	Prime	Wafer Vendor
	14.0	Edge Chips	None	Bright Light 100% (note 2)
	15.0	Edge Rounding	TBC	Wafer Vendor
HandleSilicon	15.1	Handle Thickness	675.00 +/- 5.00 um	ADE
DeviceSilicon	16.0	Haze	None	Bright Light, 100% (note 2).
	17.0	Scratches	None	Bright Light, 100% (note 2).

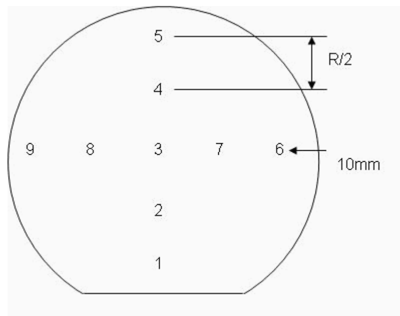
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information